Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1 - 4 (canceled).

Claim 5. (new) A power semiconductor element, comprising:

an emitter region;

a stop zone in front of said emitter region;

said emitter region and said stop zone having mutually opposite conductivities; and

said stop zone having foreign atoms, including sulfur atoms, with at least one energy level within the band gap of the semiconductor and at least 200 meV away from both a conduction band and a valence band of the semiconductor.

Claim 6 (new). A power semiconductor element, comprising:

an emitter region;

a stop zone in front of said emitter region;

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said emitter region and said stop zone having mutually opposite conductivities; and

said stop zone having foreign atoms, including selenium atoms, with at least one energy level within the band gap of the semiconductor and at least 200 meV away from both a conduction band and a valence band of the semiconductor.